

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

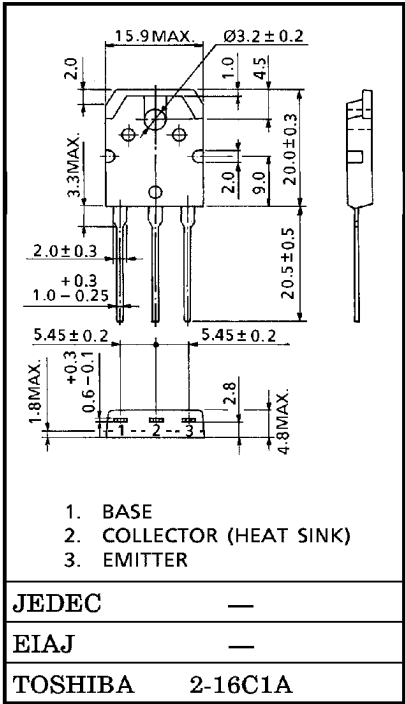
2SC5196

POWER AMPLIFIER APPLICATIONS

- Complementary to 2SA1939
- Recommend for 40W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	VCBO	80	V
Collector-Emitter Voltage	VCEO	80	V
Emitter-Base Voltage	VEBO	5	V
Collector Current	IC	6	A
Base Current	IB	0.6	A
Collector Power Dissipation (Tc= 25°C)	PC	60	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Weight : 4.7g (Typ.)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	V _{CB} =80V, I _E =0	—	—	5.0	μA
Emitter Cut-off Current	IEBO	V _{EB} =5V, I _C =0	—	—	5.0	μA
Collector-Emitter Breakdown Voltage	V (BR) CEO	I _C =50mA, I _B =0	80	—	—	V
DC Current Gain	h _{FE} (1) (Note)	V _{CE} =5V, I _C =1A	55	—	160	
	h _{FE} (2)	V _{CE} =5V, I _C =3A	35	75	—	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C =5A, I _B =0.5A	—	0.45	2.0	V
Base-Emitter Voltage	V _{BE}	V _{CE} =5V, I _C =3A	—	0.92	1.5	V
Transition Frequency	f _T	V _{CE} =5V, I _C =1A	—	30	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz	—	75	—	pF

Note : h_{FE} (1) Classification R : 55~110, O : 80~160

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